## PAIR TUNNELING IN THE LOW TEMPERATURE CONDUCTIVITY OF THE Cd-Sb ALLOY HIGH-RESISTANCE STATE NEAR THE SUPERCONDUCTOR-INSULATOR TRANSITION

V.F. Gantmakher<sup>1)</sup>, V.N. Zverev, V.T. Dolgopolov, A.A. Shashkin

Institute of Solid State Physics RAS

142432 Chernogolovka, Moscow reg., Russia

Submitted 22 October 1996

We have studied the temperature dependence, down to 30 mK, of the magnetoresistance of Cd-Sb alloy in the insulating phase that was obtained by annealing the quenched metallic superconducting  $(T_c \approx 4.5\,\mathrm{K})$  phase of the alloy. Despite the sample in this state is superconducting no more, the observed negative magnetoresistance points to single-particle tunneling in the presence of the superconducting gap in the spectrum. At magnetic fields B < 2 T the ratio  $\alpha(T,B) = R(T,B)/R(T,B=4\,\mathrm{T})$  has been found to be maximum at a temperature of about 0.1 K. This behavior indicates a change of the conductivity mechanism from single-particle tunneling to incoherent two-particle tunneling as the temperature decreases.

PACS: 71.30.+h, 72.20.Fr, 74.50.+r

The superconducting transition in the grains of a granular material promotes under some conditions an insulating behavior of the material, namely, an exponential decrease of its conductivity  $\sigma_1$  below the critical temperature  $T_c$  [1, 2]

$$\sigma_1(T) \approx \sigma_n \exp(-\Delta/T),$$
 (1)

where  $\sigma_n$  is the expected conductivity at a temperature T provided the superconductivity in the grains is absent and  $\Delta$  is the superconducting gap. Subject to the absence of dissipationless Josephson currents between the grains, the conductivity  $\sigma_1$  is determined by the single-particle tunnel current which is proportional to the exponentially small number of quasiparticles above the gap  $\Delta$ . The Josephson currents can be suppressed at the following reasons: (i) small average geometrical size d of grains results in a small capacitance C between them and thus in the destruction, due to large Coulomb energy  $e^2/2C$ , of long-range correlations of the phase of the superconducting wave function [3] (the Coulomb blockade); (ii) in tunnel junctions with large normal resistances the phase slips [4, 5]; (iii) a large fraction of the grains remains normal.

An exponential increase of the resistivity with lowering temperature, induced by the superconducting transition has been observed on ultrathin discontinuous films [1, 2] and later on three-dimensional samples [6, 7]. The phenomena can be recognized by negative magnetoresistance [2, 6]: when the magnetic field exceeds the critical value  $B_{c2}$  the superconducting gap closes and the resistance becomes  $\exp(\Delta/T)$  times smaller. In principle, measuring the ratio  $\beta = \sigma_n/\sigma_1$  gives an opportunity to extract the gap  $\Delta$  from  $\beta(T)$  and to compare it with  $T_c$ . This was done, e.g., for metastable Ga-Sb alloy [6]. However, in most cases also the normal

<sup>1)</sup>e-mail: gantm@issp.ac.ru

conductivity  $\sigma_n$  of the material turns out to depend on temperature strongly because  $\sigma_n$  is determined by hopping. This hampers analysis of the function  $\beta(T)$ . The metastable Cd-Sb alloy is an example of such a material. According to measurements from Ref. [7], the ratio  $\beta(T)$  in this alloy increases from 1.1 to 1.6 in the temperature interval from 1 K to 0.5 K, while the resistivity  $1/\sigma_n$  becomes twice as large. It is interesting to investigate the behavior of conductivities  $\sigma_1$  and  $\sigma_n$  at lower temperatures. We have performed the low temperature measurements of the high-resistance state of Cd-Sb alloy and here we present the results.

A sample of  $\mathrm{Cd_{47}Sb_{53}}$  alloy had a rod-like form with all dimensions of several millimeters. The sample was transformed into a metallic phase, which is a superconductor with  $T_c \approx 4.5\,\mathrm{K}$ , in a high-pressure chamber and quenched to the liquid-nitrogen temperature. Being cooled, the sample was clamped in a holder by two pairs of gold wires with pointed ends and placed into a cryostat. The low temperature transport measurements alternated with heating the sample to the room temperature. The heating slowly transformed the material into a disordered-insulator state. This transformation was monitored by resistance measurements and could be interrupted by returning to low temperatures. The experimental procedure is described in detail in [7].

To characterize instantaneous intermediate states of the sample we use a parameter q determined as the ratio of the sample resistances R and  $R_{in}$  in intermediate and initial states well above  $T_c$ , viz., at T=6 K:

$$q = \log(R/R_{in})_{T=6 \text{ K}}.$$

We note that R is the averaged value of resistance because in the course of the transformation the sample becomes inhomogeneous. According to Ref. [8], below  $T_c$  the sample looks like a mixture of different "weakly-superconducting" elements, such as tunnel junctions, confinements, thin wires etc. The density and scales of these elements change during transformation leading to the evolution of the sample behavior below  $T_c$  [6, 7]: with increasing q the transition first broadens, then becomes incomplete and, at q > 4, quasireentrant, i.e. at low temperatures the resistance starts to increase again. At  $q \approx 5$ , only a weak kink remains on the curve R(T) at  $T = T_c$  and the curve has a negative derivative everywhere. The  $T_c$  value slightly decreases down to  $\approx 3.8 \, \mathrm{K}$  while the average sample resistance R increases by five orders of magnitude.

The sample was transformed by steps from the metallic state q=0 to the high-resistance state  $q\approx 5$  in a He<sup>3</sup>-cryostat in a manner described in [7]. In the course of this transformation the "poorly-superconducting" states were studied. The obtained results will be published elsewhere. After q approached the value of 5, the sample was placed into Oxford TLM-400 dilution refrigerator with a base temperature of 25 mK. The low temperature measurements were performed by a four-terminal lock-in technique at a frequency of 10 Hz. An ac current was equal to 1 nA and corresponded to the linear regime. Procedures of mounting the sample into the dilution refrigerator and of its dismounting require for the sample to stay at room temperature at least for ten minutes. At this stage of transformation of Cd-Sb, such an exposure does not change the sample state significantly. This was checked after the sample had been returned into the He<sup>3</sup>-cryostat.

The experimental dependences of  $\alpha(T,B) = R(T,B)/R(T,B=4T)$  on magnetic field at different temperatures are presented in Fig.1. In the temperature range

between 490 and 190 mK the value of  $\alpha(T,0)$  increases with decreasing temperature in qualitative agreement with Eq. (1). The magnetoresistance is negative and saturates ( $\alpha \approx 1$ ) in magnetic fields exceeding 2T. This corresponds to what has been observed previously at higher temperatures [7]. However, in the low-temperature limit the behavior of  $\alpha$  changes drastically (Fig.1). In weak magnetic fields there appears an initial increase on the dependence  $\alpha(B)$  so that  $\alpha$  is maximum at  $B \approx 0.1\,\mathrm{T}$ . At a fixed magnetic field  $B < 2\,\mathrm{T}$  the value of  $\alpha$  achieves a maximum at a temperature of about 100 mK and then decreases with further lowering temperature. As seen from the inset to Fig.1, the temperature dependence of the normal state resistance is monotonous in the range of temperatures used.

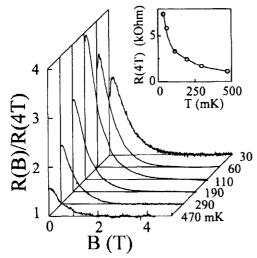


Fig.1. Magnetoresistance of the Cd-Sb sample in a state  $q\approx 5$  at different temperatures. Each curve is normalized by the value of field-independent normal state resistance taken at a field of 4T. Inset: temperature dependence of the normal state resistance

Fig.2. Change of the sample conductance with temperature. The low temperature data (circles and squares) were obtained using a dilution refrigerator and the rest data (triangles) were measured in experiment on He<sup>3</sup>-cryostat. The dashed lines fit high temperature points

One can expect that at least in strong magnetic fields the sample resistance should follow one of the activation laws typical of the hopping process. Fig.2 shows the logarithmic plot of the conductance at B=0 and B=6 T as a function of  $T^{-1/4}$ , which corresponds to the slowest of the activation dependences – the Mott law. As seen from the figure, at low temperatures both functions deviate from the Mott law and tend to saturate.

Now we will discuss these results. The observed decrease of the ratio  $\alpha$  with decreasing temperature unambiguously indicates that at low temperatures the conductivity  $\sigma_1$ , which originates from single-particle tunneling, is shunted by conductivity  $\sigma_2$  of another kind:

$$\sigma = \sigma_1(T) + \sigma_2. \tag{3}$$

We believe that  $\sigma_2$  is due to incoherent pair tunneling. Indeed, the single-particle tunneling current  $i_1$  is described in the first order approximation by barrier transparency t:  $i_1 \propto t \exp(-\Delta/T)$ . It is proportional to the product of

two small factors one of which is temperature dependent. Since Cooper pairs are at the Fermi level, two electrons forming a pair do not need to be excited above the gap for tunneling simultaneously. Hence,  $i_2 \propto t^2$ , where the exponential temperature-dependent factor is absent. When the temperature is sufficiently low

$$t > \exp(-\Delta/T), \quad \text{viz} \quad T < \Delta/|\ln t|,$$
 (4)

the single-particle current is frozen out and the two-particle tunneling comes into play.

In the second order approximation, the two-particle contribution to the tunnel current of a junction between two different superconductors (SIS junction) has been calculated in Ref. [9]. Given a SIS junction with gaps  $\Delta$  and  $\Delta_1$ , the two-particle current is significant above the threshold voltage  $eV = \min(\Delta, \Delta_1)$ . For tunneling into a normal metal (SIN junction,  $\Delta_1 = 0$ ) the threshold is absent. Therefore the resistance of SIN junction is finite at zero temperature. The two-electron tunneling in a SIN junction with high-resistance barrier has been studied in detail in Ref. [10].

Let us consider percolation on a simple cubic lattice (critical concentration  $X^{(s)} = 0.31$  for the site percolation and  $X^{(b)} = 0.25$  for the bond percolation [11]) with concentrations  $x_n < X^{(s)}$  of normal (N) grains and  $x_s = 1 - x_n$  of superconducting (S) grains in the sites of the lattice. The resistance of the lattice is determined by three types of contacts (bonds): SS with concentration  $x_s^2$ , SN with concentration  $2x_n x_n$  and NN with concentration  $x_n^2$ . According to Ref. [7], in magnetic fields above 0.1 T Josephson currents through SS bonds are suppressed, if any, and so at relatively high temperatures all SS and SN junctions are in the  $\sigma_1$ -regime. When the temperature becomes lower than the threshold (4), SS junctions remain in the poor  $\sigma_1$ -regime so that the conductance is governed by the network of SN junctions. Their concentration may be rather large even at small  $x_n$ ; for instance, when  $x_n = 0.15$  (half of the critical value  $X^{(s)}$ ), the concentration  $x_{sn}$  exceeds 0.25, which is sufficient for percolation. For interpreting a maximum on the experimental dependence R(B) at low temperatures one has to suggest that in fields below 0.1 T Josephson currents through some SS bonds are not negligible. Still, it is difficult to explain why the region of the positive magnetoresistance shrinks at higher temperatures (Fig.1).

Obviously, the line of reasoning above implies that the size of grains is macroscopic, i.e., large compared to the relevant lengths. One of them, the coherence length  $\xi$ , can be easily estimated. The characteristic field  $B_{ch}$  in superconductivity is related to the essential length  $\lambda_{ch}$  by the expression

$$B_{ch} = \Phi_0/2\pi\lambda_{ch}^2, \qquad \Phi_0 = h/2e.$$
 (5)

If the field  $B_{c2}$  is in question, then, dependent on the relation between the coherence length  $\xi$  and the mean free path  $\ell$ , the length  $\lambda_{ch}$  is written as [12]

$$\lambda_{ch} = \xi, \qquad \ell \gg \xi \qquad \text{(pure limit)},$$

$$\lambda_{ch} = (\xi \ell)^{1/2}, \qquad \ell \ll \xi \qquad \text{(dirty limit)}.$$
(6)

According to the experimental data, a field 2T destroys the remnants of the superconductivity and should be regarded as  $B_{c2}$ . Then, from the above relation in the pure limit we get an estimation for the coherence length  $\xi \geq 120$  Å.

The other relevant length follows from the comparison of the size quantization  $\delta \varepsilon \approx (g_F d^3)^{-1}$  (here  $g_F$  is the density of states at the Fermi level) and  $\Delta$ : a separate grain cannot remain superconducting if  $\Delta < \delta \varepsilon$ . The critical grain size  $d_c$  proves to be even smaller than  $\xi$ .

Experimental estimates of the length d which determines the randomness of the structure are rather uncertain. Insensitivity of the field  $B_{c2}$  to the transformation parameter q implies  $d > \xi$ . As an alternative, authors of Ref. [8] argue that in transforming the sample into a high-resistance state the length d decreases until any macroscopic structure vanishes. Below we will show that the conclusion about the change of the conductivity mechanism from single-particle tunneling to incoherent two-particle tunneling is valid also at smaller than  $d_c$  dimensions of grains in terms of a concept of localized Cooper pairs in a quasihomogeneous disordered material [13].

If there exists a field-dependent attractive interaction between two electrons localized on different centers at a distance smaller than  $\xi$ , they can be regarded as a localized Cooper pair [14]. For an electron of the pair to hop, it has to pay off the binding energy  $\Delta$ . However, two interacting electrons remain bounded if their hops are correlated [15]. If the Cooper interaction fluctuates depending on the mutual disposition of electron sites, the binding energy  $\Delta_1$  in a final state may differ from that in an initial state. The final state can be even unbound, see Fig.3. The energies of states  $l_0$  and  $l_0$  are well above the Fermi level if at least one of these states is empty. When both states are occupied they descend, due to the Cooper interaction, toward the Fermi level to energies  $l_i$  and  $l_i$ . The final state energies  $l_i$  and  $l_i$  do not depend on occupation numbers if either a barrier between the states is high (Fig.3a) or they are far from one another (Fig. 3b).

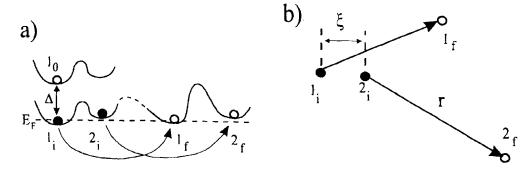


Fig.3. Two electron hop from interacting states  $1_i$  and  $2_i$  to noninteracting states  $1_f$  and  $2_f$  in energy scheme (a) and geometrical scheme (b). If only one of these electrons hopped the other would have to increase its energy by  $\Delta$  (to the level  $1_0$  or, correspondingly,  $2_0$ ).

The appearance of a maximum on R(B) at  $\approx 0.1$  T at low temperatures can be explained by a reduction of the probability of pair hopping with magnetic field, which gives rise to an initial increase of the resistance R in weak magnetic fields. In this connection, we shall revisit the expression (5) that compares the magnetic flux through an area  $\lambda_{ch}^2$  with the flux quantum  $\Phi_0$ . This relation is met not only in superconductivity but also in the theories of weak localization and of interference in hopping. According to [10], the interference is of prime importance for two-electron tunneling through high-resistance barriers. One can expect that

the interference should be destroyed in a typical magnetic field determined by the relevant length. In the granular model this can be the coherence length  $\xi$ , the grain size d, the phase-breaking length  $L_{\varphi}$ , and the mean free path  $\ell$ . In the localized pair model,  $\xi$  and the hopping distance r should be important. Thus, assuming that localized pair hops are present one can account for the positive magnetoresistance observed in weak fields. However, there is no theory yet to make comparison with.

The tendency to saturation of the normal state resistance at low temperatures (Fig.2) points to the existence of a shunting conductivity (cf. [16]) which may, e.g., be due to the resonant tunneling of localized electrons.

In summary, we have investigated the temperature and magnetic field dependence of the resistance of the metastable Cd-Sb alloy transformed into a high-resistance state. It has been established that below  $T_c$  the behavior of the resistance is determined by the competition between single-particle tunneling and incoherent two-particle tunneling. Considering the two limiting cases of macroscopic grains in the sample and of a quasihomogeneous material in terms of localized Cooper pairs we argue that regardless of grain dimension, the incoherent pair tunneling is dominant in the low-temperature limit.

We are grateful to M.V.Feigelman and A.I. Larkin for discussions. This work was supported in part by the Russian Foundation for Basic Research under Grant 96-02-17497, by the Programme "Statistical Physics" from the Russian Ministry of Sciences and by INTAS RFBR under Grant 95-0302.

- 1. R.C.Dynes, J.P.Garno, and J.M.Rowell, Phys. Rev. Lett. 40, 479 (1978).
- 2. C.J.Adkins, J.M.D.Thomas, and M.W.Young, J. Phys. C 13, 3427 (1980).
- 3. K.B.Efetov, Sov. Phys. JETP 51, 1015 (1980).
- 4. A.Schmid, Phys. Rev. Lett. 51, 1506 (1983).
- 5. M.P.A.Fisher, Phys. Rev. Lett. 57, 885 (1986).
- 6. V.F.Gantmakher, V.N.Zverev, V.M.Teplinskii et al., JETP 77, 513 (1993).
- 7. V.F.Gantmakher, V.N.Zverev, V.M.Teplinskii, and O.I.Barkalov, JETP 78, 226 (1994).
- 8. V.F.Gantmakher, S.E.Esipov, and V.M.Teplinskii, JETP 70, 211 (1990).
- 9. Yu.N.Ovchinnikov, R.Christiano, and C.Nappi, J. Low Temp. Phys. 99, 81 (1995).
- 10. F.W.J.Hekking and Yu.V.Nazarov, Phys. Rev. B 49, 6847 (1994).
- 11. D.Stauffer, Introduction to percolation theory, Taylor and Fransis, 1985.
- 12. A.A.Abrikosov, Fundamentals of the Theory of Metals, North-Holland, 1988.
- 13. E.S.Soerensen, M.Wallin, S.M.Girvin, and A.P.Young, Phys. Rev. Lett. 69, 828 (1992).
- 14. V.F.Gantmakher, M.V.Golubkov, J.G.S.Lok, and A.K.Geim, JETP 82, 951 (1996).
- 15. Y.Imry, Europhys. Lett. 30, 405 (1995).
- 16. I.V.Lerner and Y.Imry, Europhys. Lett. 29, 49 (1995).